

# (A-021-DOT) DC-AC 3-Phase Vienna PFC (DOT247)

## Simulation Parameters

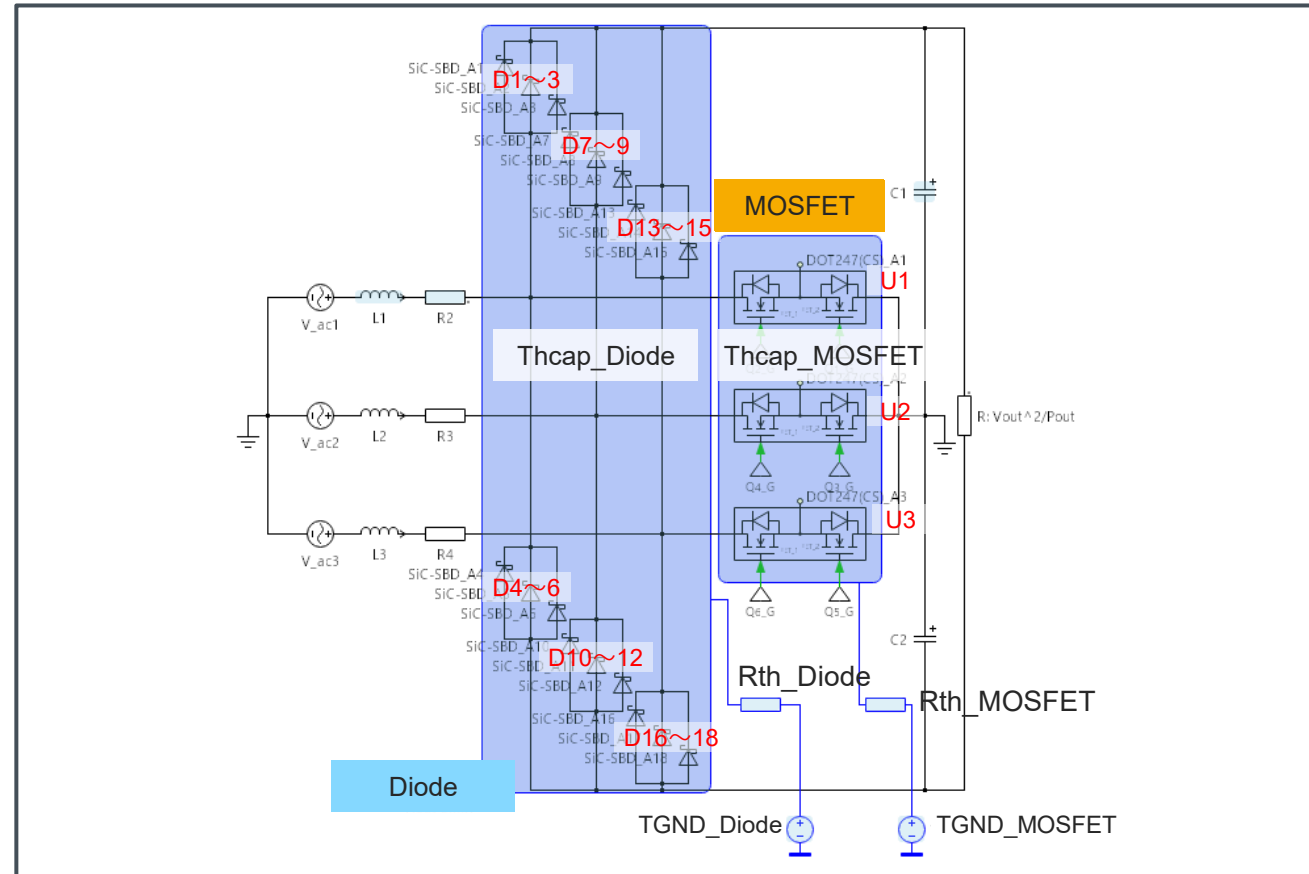
Name	Content	unit	Default Value	Variable Range
L1~3	Inductive Load	H	470u	1n ~ 1
R2~4	Choke Resistance	Ω	5m	1u ~ 100m
C1,C2	Output Capacitor Initial Voltage	F V	1m 400	1n ~ 1 0 ~ 1200
Thcap_MOSFET	Thermal Capacitance	J/K	0.1	1m ~ 100
Rth_MOSFET	Thermal Resistance	K/W	1	1m ~ 100
TGND_MOSFET	Thermal GND Temperature	°C	25	-40 ~ 175
Thcap_Diode	Thermal Capacitance	J/K	0.1	1m ~ 100
Rth_Diode	Thermal Resistance	K/W	1	1m ~ 100
TGND_Diode	Thermal GND Temperature	°C	25	-40 ~ 175

Name	Content	unit	Default Value	Variable Range
Test_time	Test time in simulation	s	0.5	100u ~ 0.5
fs	Switching Frequency	Hz	12k	10k ~ 100k
Vin_ac (rms)	Input Voltage (Peak Voltage) Grid Frequency	V Hz	220 50	100 ~ 500 50 or 60
Vout_dc	Output Voltage	V	800	300 ~ 1200
Pout	Output Power	W	25000	100 ~ 33000
Rg_on*	Gate Resistance (Source)	Ω	6.8	0.1 ~ 100
Rg_off*	Gate Resistance (Sink)	Ω	4.7	0.1 ~ 100
T_init**	Initial Junction Temp.	°C	25	-40 ~ 175

\*Same value for all MOSFETs

\*\*Same value for all devices

## Simulation Circuit

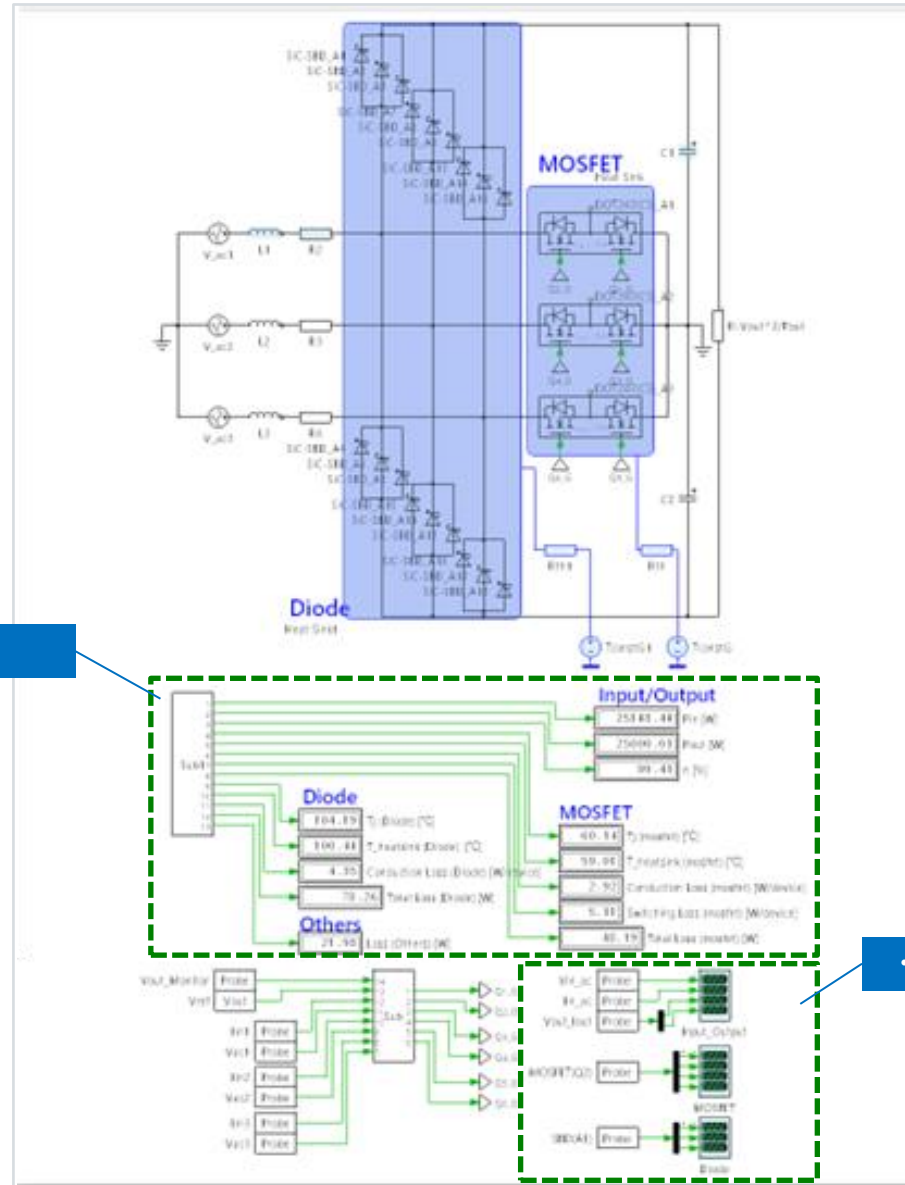


## Default Devices

Name	Device Type	Part No.	Specification
U1~3	SiC MOSFET Module	SCZ4004DTB	750V/ 251A/ 4mΩ/ DOT247(Common Source)
D1~18	SiC SBD*	SCS320AG	650V/ 20A/ TO-220ACGE

\*SBD:Schottky Barrier Diode

## Schematic window

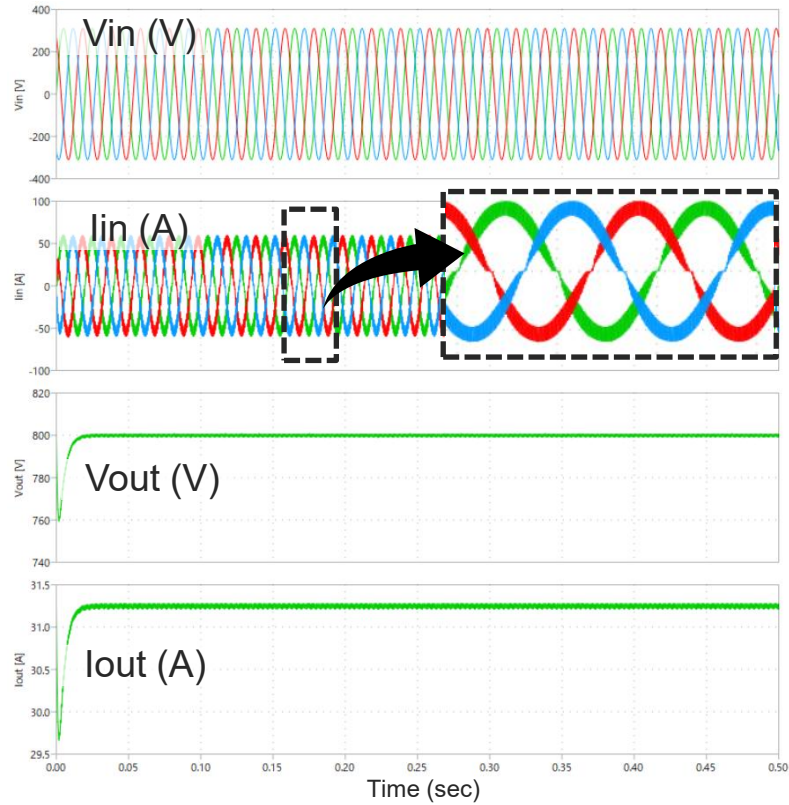


•Results display

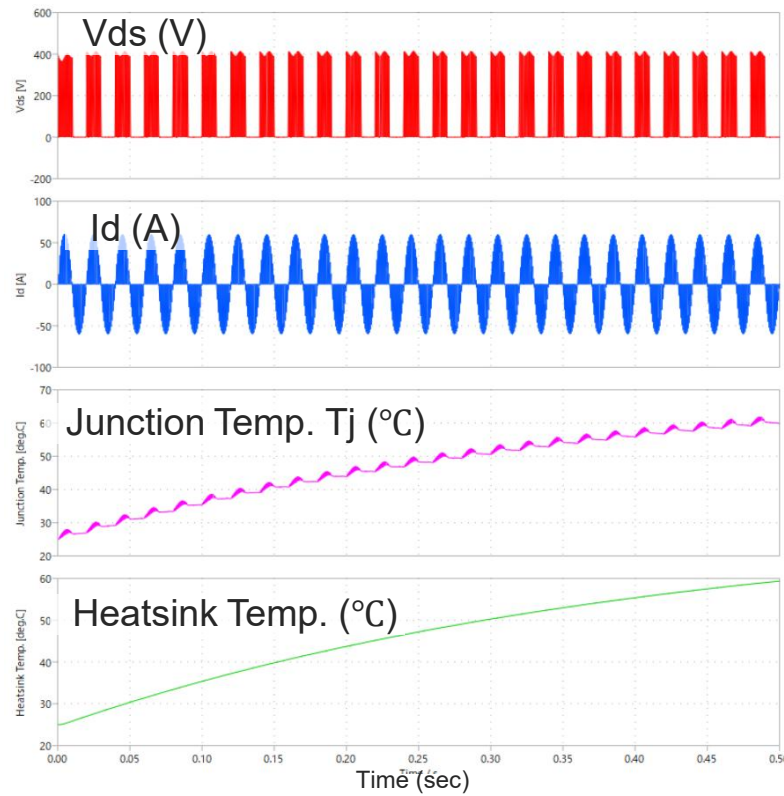
•Scope the waveform

# Simulation Results

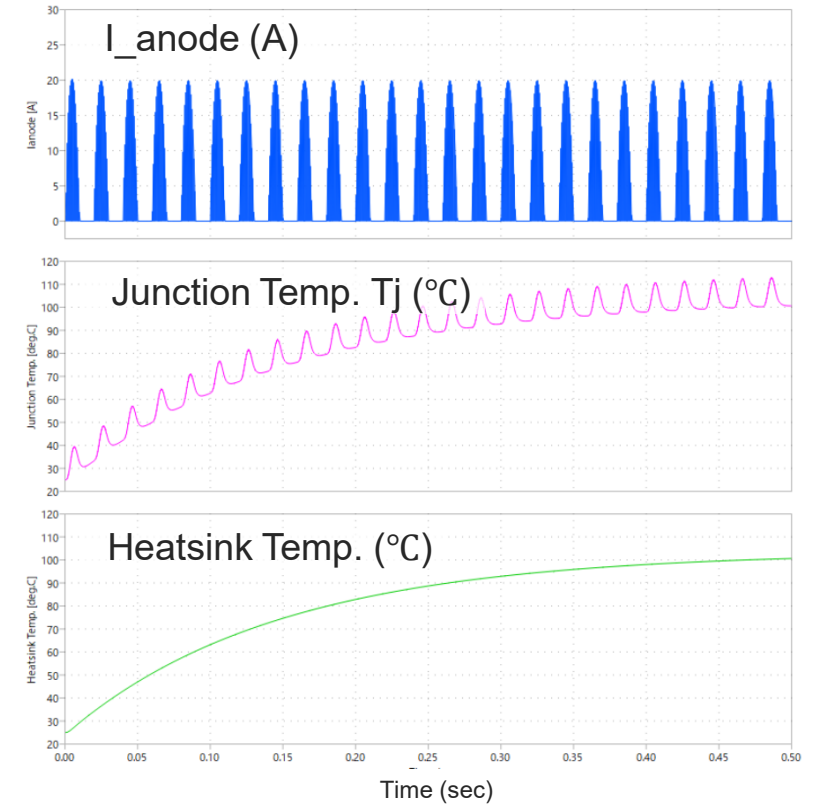
## Input and Output



## MOSFET



## Diode



Contents	Results
Input Power : $P_{in}$	25.148 (kW)
Output Power: $P_{out}$	25.000 (kW)
Efficiency: $\eta$	99.41 (%)

Contents	Results
Junction Temp. $T_j$ (mosfet)	60.14 (°C)
Heatsink Temp. $T_{hs}$ (mosfet)	59.01 (°C)
Conduction Loss: $P_{cond}$ (mosfet)	2.92 (W/device)
Switching Loss: $P_{sw}$ (mosfet)	5.11 (W/device)
Total Loss: $P_{tot}$ (mosfet)	48.19 (W)

Contents	Results
Junction Temp. $T_j$ (diode)	104.19 (°C)
Heatsink Temp. $T_{hs}$ (diode)	100.44 (°C)
Conduction Loss: $P_{cond}$ (diode)	4.35 (W/device)
Total Loss: $P_{tot}$ (diode)	78.26 (W)

To run this PLECS Reference Circuit, you must have the "PLECS" simulation software installed on your computer.

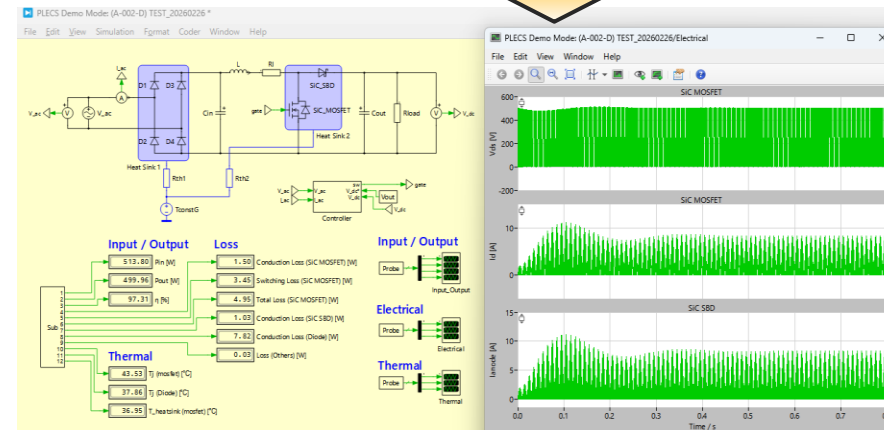
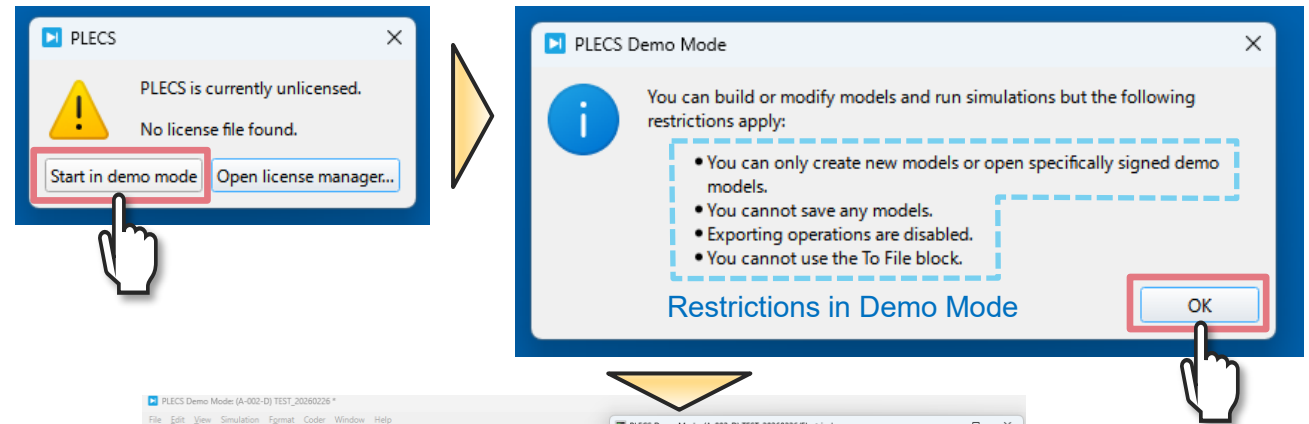
## 1. Obtaining the Software

If you do not have PLECS installed, please download the installer from the official website and complete the setup process.

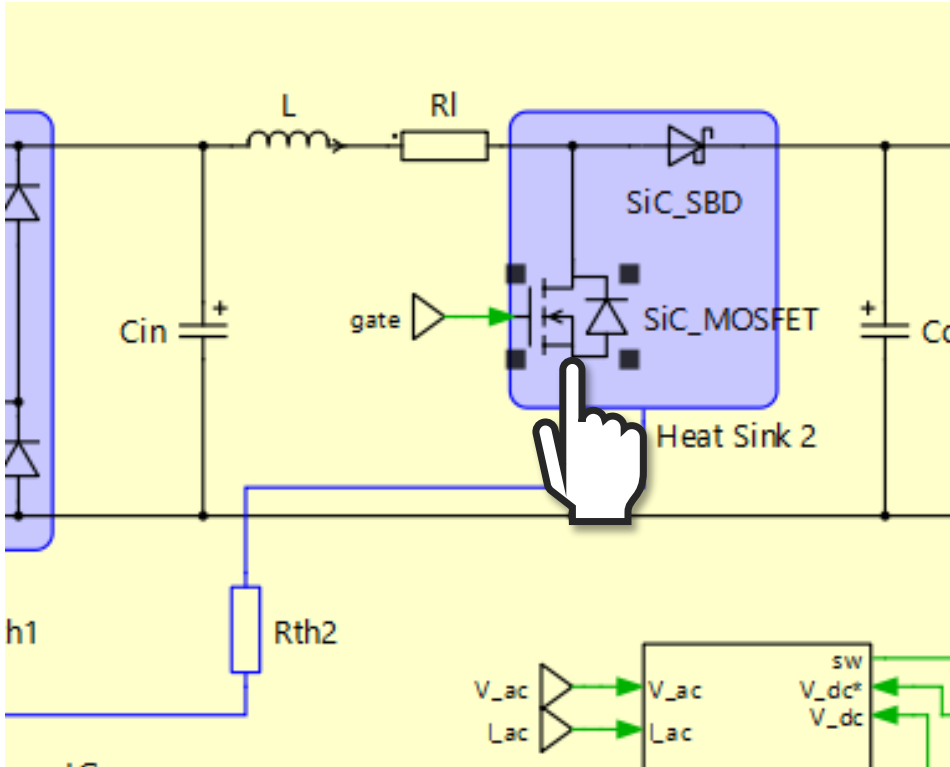
<https://www.plexim.com/download>

## 2. Licensing (Using Demo Mode)

This reference circuit can be executed and viewed in "Demo Mode" even if you do not possess a paid license.



## Schematic window



Block Parameters: (A-002-D) AC-DC Boost PFC Diode Rectific... X

SiC-MOSFET (mask)

Model Generated by ROHM  
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Date: 21-Jan.-2026

Parameters Assertions

SiC-MOSFET:  
SiCMOS

Custom variables:  
struct('Rg\_on', 'Rg\_on', 'Rg\_off', 'Rg\_off', 'sw', 'sw')

Gate resistance (on):  
Rg\_on

Gate resistance (off):  
Rg\_off

Initial temperature:  
T\_init

Initial Ron:  
Ron\_init

OK Cancel Apply Help

- From library...
- By reference
- Edit...
- Remove
- New thermal description...
- New thermal package description...

[SiC-MOSFET] TO-247-4L\_750V\_25A\_65mΩ (SCT4065DR)  
[SiC-MOSFET] TO-247-4L\_750V\_34A\_45mΩ (SCT4045DR)  
[SiC-MOSFET] TO-247-4L\_750V\_42A\_36mΩ (SCT4036DR)  
[SiC-MOSFET] TO-247-4L\_750V\_56A\_26mΩ (SCT4026DR)  
[SiC-MOSFET] TO-247N\_1200V\_19A\_90mΩ (SCT4090KE)  
[SiC-MOSFET] TO-247N\_1200V\_26A\_62mΩ (SCT4062KE)  
[SiC-MOSFET] TO-247N\_1200V\_32A\_50mΩ (SCT4050KE)  
[SiC-MOSFET] TO-247N\_1200V\_40A\_36mΩ (SCT4036KE)  
[SiC-MOSFET] TO-247N\_1200V\_81A\_18mΩ (SCT4018KE)  
[SiC-MOSFET] TO-247N\_750V\_105A\_13mΩ (SCT4013DE)  
[SiC-MOSFET] TO-247N\_750V\_25A\_65mΩ (SCT4065DE)  
[SiC-MOSFET] TO-247N\_750V\_34A\_45mΩ (SCT4045DE)  
[SiC-MOSFET] TO-247N\_750V\_42A\_36mΩ (SCT4036DE)  
[SiC-MOSFET] TO-247N\_750V\_56A\_26mΩ (SCT4026DE)  
[SiC-MOSFET] TO-263-7LA\_1200V\_17A\_90mΩ (SCT4090KWA)  
[SiC-MOSFET] TO-263-7LA\_1200V\_24A\_62mΩ (SCT4062KWA)  
[SiC-MOSFET] TO-263-7LA\_1200V\_29A\_50mΩ (SCT4050KWA)  
[SiC-MOSFET] TO-263-7LA\_1200V\_40A\_36mΩ (SCT4036KWA)  
[SiC-MOSFET] TO-263-7LA\_1200V\_75A\_18mΩ (SCT4018KWA)  
[SiC-MOSFET] TO-263-7LA\_750V\_22A\_65mΩ (SCT4065DWA)  
[SiC-MOSFET] TO-263-7LA\_750V\_31A\_45mΩ (SCT4045DWA)  
[SiC-MOSFET] TO-263-7LA\_750V\_38A\_36mΩ (SCT4036DWA)  
[SiC-MOSFET] TO-263-7LA\_750V\_51A\_26mΩ (SCT4026DWW)  
[SiC-MOSFET] TOLL\_750V\_120A\_13mΩ (SCT4013DLL)  
[SiC-MOSFET] TOLL\_750V\_26A\_65mΩ (SCT4065DLL)  
[SiC-MOSFET] TOLL\_750V\_37A\_45mΩ (SCT4045DLL)

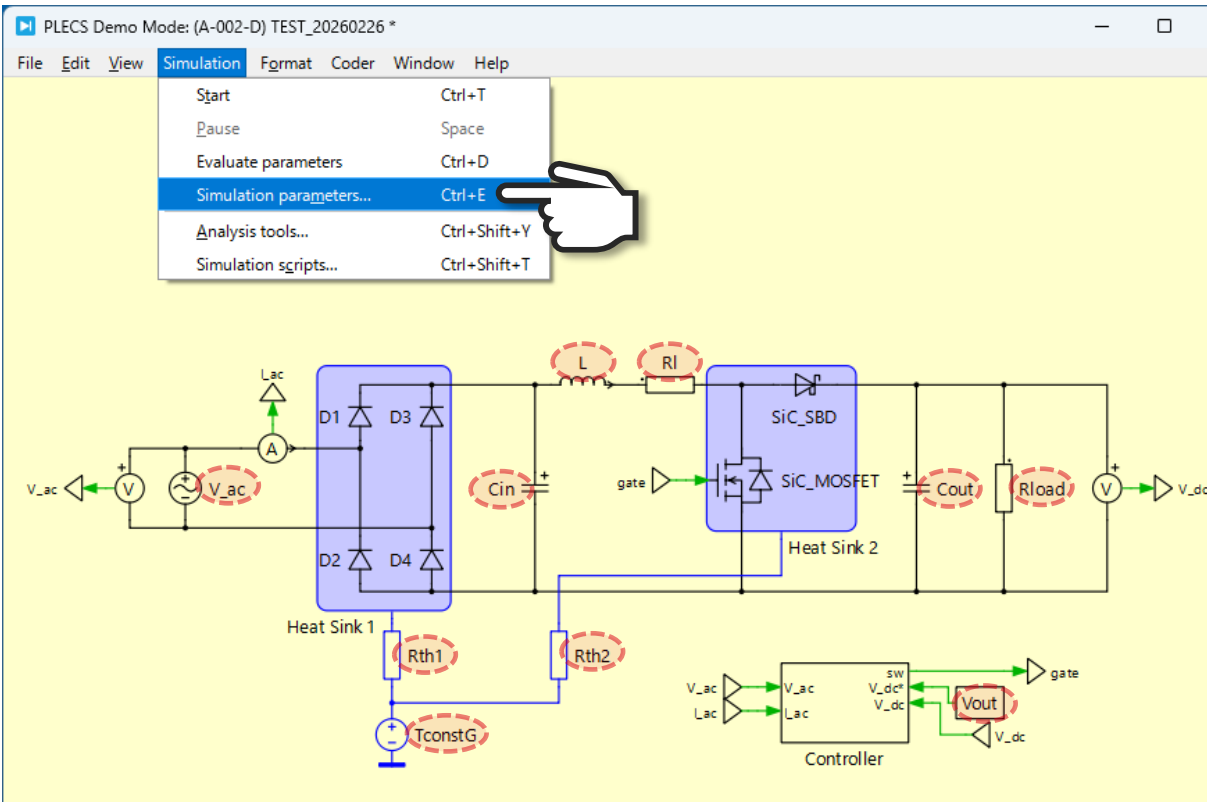
Hover your mouse cursor over the device symbol that you want to change and double-click the left button of the mouse.

Click "... " > "From library..." to view the list of available devices and you can select a favorite device from these.

If the model you need is not in the list, please refer to the application note "[How to Use PLECS Models](#)".

# How to change the simulation parameters

## Schematic window



```
1 % General|
2 Test time = 0.8; % End time of simulation [s]
3 SiCMOS = 'file:SC14065DR';
4 SiCSBD = 'file:SCS320AG';
5
6 % Grid
7 Vin = 100;
8 %Wac = Vin*sqrt(2); % Grid voltage [V]
9 Vout = 500
10 F = 50.0; % Grid frequency [Hz]
11
12 % Plant
13 fs_k = 50; % Switching frequency [kHz]
14 %fs = fs_k*1e3; % Switching frequency [Hz]
15
16 Rl = 0.001
17 Rload = 500; % Load resistance [ohms]
18 Rsense = 0.0025; % Sense resistance [ohms]
19 L = 1e-3; % Choke inductance [H]
20 Cin = 0.1e-6; % Input capacitor [C]
21 Cout = 1e-3; % Output capacitor [C]
22 C1 = 470e-9; % Reference capacitor [C]
23
24 %Wcout_init = Vout; %Initial Voltage of Output Capacitor [V]
25
26
27 R_Di = 0.02; % Diode On-resistance [ohm]
28 V_F_Di = 0.6; % Diode On-resistance [ohm]
29
30 % Thermal system
31 T_init = 25; % Initial Temperature of Heatsink [deg.C]
32 Thcap_1 = 0.001; % Thermal capacitance of Heatsink [J/K]
33 Thcap_2 = 0.001; % Thermal capacitance of Heatsink [J/K]
34 Rth_1 = 2.0; % Thermal Resistance [K/W]
35 Rth_2 = 2.0; % Thermal Resistance [K/W]
36 T_GND = 25; %Thermal GND Temperature [deg.C]
37
```

All simulation parameters are parameterized. To modify them, go to the menu, select “Simulation parameters...”, and edit the values within “Model initialization commands.”

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